

ABSTRACT

A light-emitting thyristor having an improved luminous efficiency is provided. According to the light-emitting thyristor, a p-type AlGaAs layer and an n-type AlGaAs layer
5 are alternately stacked to form a pnpn structure on a GaAs buffer layer formed on a GaAs substrate, and Al composition of the AlGaAs layer just above the GaAs buffer layer is increased in steps or continuously.

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